

8 k × 8 NONVOLATILE SRAM (5 V, 3.3 V)

FEATURES

- Data Retention for at least 10 Years Without Power
- Automatic Write-Protection During Power-up/Power-down Cycles
- Conventional SRAM Operation, Including Unlimited Write Cycles
- Internal Isolation of Battery before Power Application
- 5-V or 3.3-V Operation
- Industry Standard 28-Pin DIP Pinout or 34-Pin LIFETIME LITHIUM™ SMD Pinout
- Snap-on, Replaceable Lithium Battery for SMD Device
(Device Number: bq401BATCAP)

GENERAL DESCRIPTION

The CMOS bq4010/Y/LY is a nonvolatile 65,536-bit static RAM organized as 8,192 words by 8 bits. The integral control circuitry and lithium energy source provide reliable nonvolatility coupled with the unlimited write cycles of standard SRAM.

The control circuitry constantly monitors the single supply for an out-of-tolerance condition. When V_{CC} falls out of tolerance, the SRAM is unconditionally write-protected to prevent an inadvertent write operation.

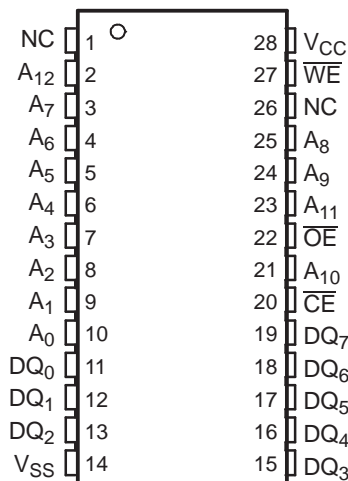
At this time the integral energy source is switched on to sustain the memory until after V_{CC} returns valid.

The bq4010/Y/LY uses extremely low standby current CMOS SRAMs, coupled with small lithium coin cells to provide nonvolatility without long write-cycle times and the write-cycle limitations associated with EEPROM.

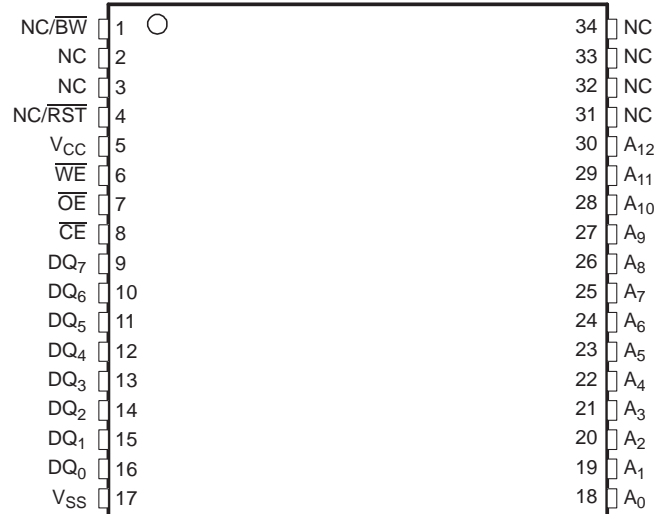
The bq4010/Y/LY requires no external circuitry and is compatible with the industry-standard 64-Mb SRAM pinout.

PIN CONNECTIONS

28-Pin DIP Module
(TOP VIEW)



34-Pin
Lifetime Lithium Module
(TOP VIEW)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DEVICE INFORMATION**Table 1. TERMINAL FUNCTIONS**

NAME	TERMINAL			I/O	DESCRIPTION
	DIP-28	LLM-34 V _{CC} = 3.3 V	LLM-34 V _{CC} = 5 V		
A ₀	10	18	18	I	Address inputs
A ₁	9	19	19	I	
A ₂	8	20	20	I	
A ₃	7	21	21	I	
A ₄	6	22	22	I	
A ₅	5	23	23	I	
A ₆	4	24	24	I	
A ₇	3	25	25	I	
A ₈	25	26	26	I	
A ₉	24	27	27	I	
A ₁₀	21	28	28	I	
A ₁₁	23	29	29	I	
A ₁₂	2	30	30	I	
\overline{BW}	-	1	-	O	Battery warning output (open drain)
CE	20	8	8	I	Chip-enable input
DQ ₀	11	16	16	I/O	Data input/output
DQ ₁	12	15	15	I/O	
DQ ₂	13	14	14	I/O	
DQ ₃	15	13	13	I/O	
DQ ₄	16	12	12	I/O	
DQ ₅	17	11	11	I/O	
DQ ₆	18	10	10	I/O	
DQ ₇	19	9	9	I/O	
NC	1	-	1	-	No connect
	-	2	2		
	-	3	3		
	-	-	4		
	26	-	-		
	-	31	31		
	-	32	32		
	-	33	33		
	34	34			
\overline{OE}	22	7	7	I	Output enable input
\overline{RST}	-	4	-	O	Power-up reset to system CPU output (open drain)
V _{CC}	28	5	5	I	Supply voltage input
V _{SS}	14	17	17	-	Ground
\overline{WE}	27	6	6	I	Write enable input

FUNCTIONAL DESCRIPTION

When power is valid, the bq4010/Y/LY operates as a standard CMOS SRAM. During power-down and power-up cycles, the bq4010/Y/LY acts as a nonvolatile memory, automatically protecting and preserving the memory contents.

Power-down/power-up control circuitry constantly monitors the V_{CC} supply for a power-fail-detect threshold V_{PFD} . The bq4010 monitors for $V_{PFD} = 4.62$ V typical for use in 5-V systems with 5% supply tolerance. The bq4010Y monitors for $V_{PFD} = 4.37$ V typical for use in 5-V systems with 10% supply tolerance. The bq4010LY monitors for $V_{PFD} = 2.90$ V (typ) for use in 3.3-V systems.

When V_{CC} falls below the V_{PFD} threshold, the SRAM automatically write-protects the data. All outputs become high impedance, and all inputs are treated as *don't care*. If a valid access is in process at the time of power-fail detection, the memory cycle continues to completion. If the memory cycle fails to terminate within time t_{WPT} , write-protection takes place.

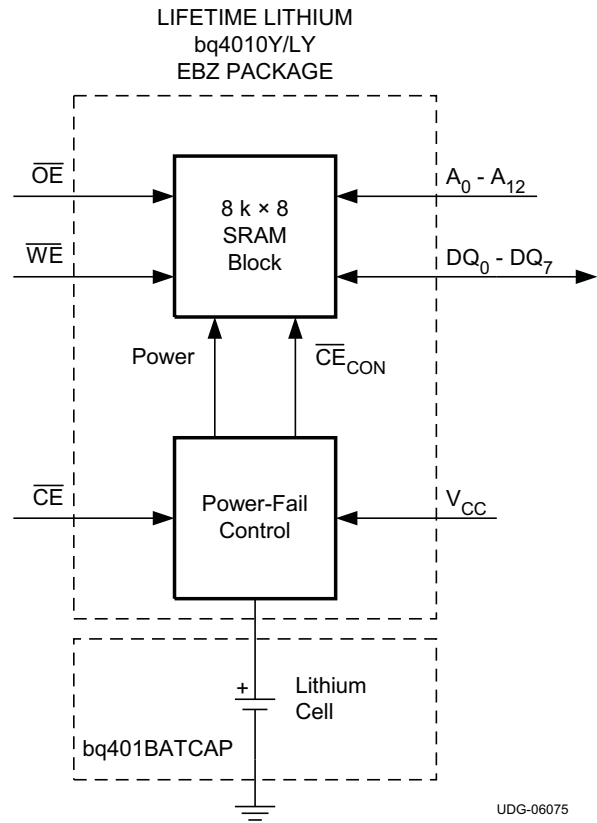
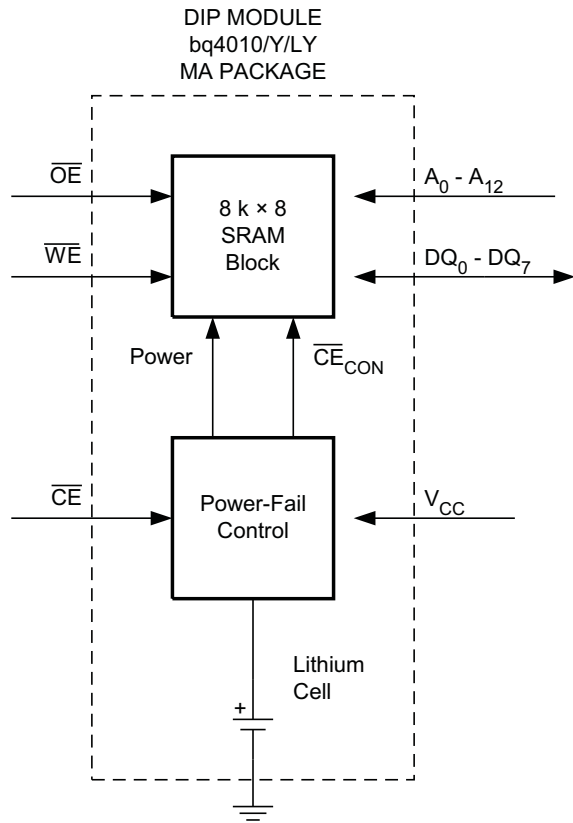
As V_{CC} falls past V_{PFD} and approaches V_{SO} , the control circuitry switches to the internal lithium backup supply, which provides data retention until valid V_{CC} is applied.

When V_{CC} returns to a level above the internal backup cell voltage, the supply is switched back to V_{CC} . After V_{CC} ramps above the V_{PFD} threshold, write-protection continues for a time t_{CER} (120 ms maximum in 5-V system, 85 ms maximum in 3.3-V system) to allow for processor stabilization. Normal memory operation may resume after this time.

The internal coin cells used by the bq4010/Y/LY have an extremely long shelf life and provide data retention for more than 10 years in the absence of system power.

As shipped from TI, the integral lithium cells of the MT-type module are electrically isolated from the memory. (Self-discharge in this condition is approximately 0.5% per year.) Following the first application of V_{CC} , this isolation is broken, and the lithium backup provides data retention on subsequent power-downs. The LIFETIME LITHIUM package option is shipped as two devices, which must be ordered separately.

BLOCK DIAGRAM



UDG-06075

ORDERING INFORMATION

For the most current package and ordering information, see the Package Option Addendum at the end of the datasheet, or see the TI website at www.ti.com.

SELECTION GUIDE

DEVICE NUMBER	MAXIMUM ACCESS TIME (ns)	NEGATIVE SUPPLY TOLERANCE (%)	NOMINAL INPUT VOLTAGE V_{CC} (V)	TEMPERATURE (°C)	MODULE		
bq4010MA-70	70	-5	5	0 to 70	DIP		
bq4010MA-85	85						
bq4010MA-150	150						
bq4010MA-200	200						
bq4010YMA-70	70						
bq4010YMA-85	85						
bq4010YMA-150	150						
bq4010YMA-200	200						
bq4010YMA-70N	70	-10		3.3		-40 to 85	Lifetime Lithium
bq4010YMA-85N	85						
bq4010YMA-150N	150						
bq4010YEBZ-70N	70						
bq4010LYMA-70N			DIP				
bq4010LYEBZ-70N			Lifetime Lithium				

PART NUMBERING

PRODUCT LINE	MEMORY DENSITY	INPUT VOLTAGE (V)	NEGATIVE SUPPLY TOLERANCE	PACKAGE	SPEED (ns)	TEMPERATURE (°C)
bq40	10	L	Y	MA	70	N
	10 = 8 k × 8	Blank = 5	Blank = 5%	MA = DIP	70	Blank = Commercial
	11 = 32 k × 8	L = 3.3	Y = 10%	EBZ = SMD	85	(0 to 70)
	13 = 128 k × 8				100	
	14 = 256 k × 8				120	N = Industrial
	15 = 512 k × 8				150	(-40 to 85)
	16 = 1024 k × 8				200	
	17 = 2048 k × 8					

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

PARAMETER		CONDITION	VALUE	UNIT	
V _{CC}	DC voltage applied on VCC relative to VSS	bq4010Y	-0.3 to 7.0	V	
		bq4010	-0.3 to 7.0		
		bq4010LY	-0.3 to 6.0		
V _T	DC voltage applied on any pin excluding VCC relative to VSS	V _{VT} ≤ V _{CC} + 0.3 V	bq4010Y	-0.3 to 7.0	V
			bq4010	-0.3 to 7.0	
			bq4010LY	-0.3 to (V _{CC} + 0.3)	
T _{OPR}	Operating temperature	Commercial	0 to 70	°C	
		Industrial	-40 to 85		
T _{STG}	Storage temperature	Commercial	-10 to 70		
		Industrial	-40 to 85		
T _{BIAS}	Temperature under bias	Commercial	-10 to 70		
		Industrial	-40 to 85		
T _{SOLDER}	Soldering temperature	For 10 seconds	260		

(1) Permanent device damage may occur if **Absolute Maximum Ratings** are exceeded. Functional operation should be limited to the Recommended DC Operating Conditions detailed in this data sheet. Exposure to conditions beyond the operational limits for extended periods of time may affect device reliability.

RECOMMENDED OPERATING CONDITIONS (T_A = T_{OPR})

		MIN	TYP ⁽¹⁾	MAX	UNIT	
V _{CC}	Supply voltage	bq4010Y	4.50	5.00	5.50	V
		bq4010	4.75	5.00	5.50	
		bq4010LY	3.00	3.30	3.60	
V _{SS}	Supply voltage	0	0	0		
V _{IL}	Low-level input voltage	-0.3		0.8		
V _{IH}	High-level Input voltage	2.2		V _{CC} + 0.3		

(1) Typical values indicate operation at T_A = 25°C.

CAPACITANCE (T_A = 25°C, f = 1 MHz, V_{CC} = 5.0 V or V_{CC} = 3.3 V)

PARAMETER ⁽¹⁾		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C _{I/O}	Input/output capacitance	Output voltage = 0 V			8	pF
C _{IN}	Input capacitance	Input voltage = 0 V			10	

(1) Ensured by design. Not production tested.

DC ELECTRICAL CHARACTERISTICS

T_A = T_{OPR}, V_{CC(min)} ≤ V_{CC} ≤ V_{CC(max)}

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT	
I _{LI}	Input leakage current	V _{IN} = V _{SS} to V _{CC}			±1	μA	
I _{LO}	Output leakage current	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$			±1		
V _{OH}	Output high voltage	I _{OH} = -1.0 mA	2.4			V	
V _{OL}	Output low voltage	I _{OL} = 2.1 mA			0.4		
I _{SB1}	Standby supply current	$\overline{CE} = V_{IH}$		1	2	μA	
I _{SB2}	Standby supply current	$\overline{CE} \geq V_{CC} - 0.2$ V, 0V ≤ V _{IN} ≤ 0.2 V, or V _{IN} ≥ V _{CC} - 0.2		0.1	1	mA	
I _{CC}	Operating supply current	bq4010	Minimum cycle, duty = 100%, $\overline{CE} = V_{IL}$, I _{I/O} = 0 mA			35	mA
		bq4010Y					
		bq4010LY				30	

(1) Typical values indicate operation at T_A = 25°C, V_{CC} = 5.0 V or V_{CC} = 3.3 V.

DC ELECTRICAL CHARACTERISTICS (continued)

$$T_A = T_{OPR}, V_{CC(min)} \leq V_{CC} \leq V_{CC(max)}$$

PARAMETER			TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{PFD}	Power-fail-detect voltage	bq4010		4.55	4.62	4.75	V
		bq4010Y		4.30	4.37	4.50	
		bq4010LY		2.85	2.90	2.95	
V _{SO}	Supply switch-over voltage	bq4010		3			
		bq4010Y		3			
		bq4010LY		2.9			

TRUTH TABLE

MODE	\overline{CE}	\overline{WE}	\overline{OE}	I/O OPERATION	POWER
Not selected	H	X	X	High-Z	Standby
Output disable	L	H	H	High-Z	Active
Read	L	H	L	D _{OUT}	Active
Write	L	L	H	D _{IN}	Active

AC TEST CONDITIONS

PARAMETER	TEST CONDITIONS	
	5 V	3.3 V
Input pulse levels	0 V to 3.0 V	0 V to V _{CC}
Input rise and fall times	5 ns	5 ns
Input and output timing reference levels	1.5 V (unless otherwise specified)	50 %
Output load (including scope and jig)	See Figure 1 and Figure 2	See Figure 3 and Figure 4

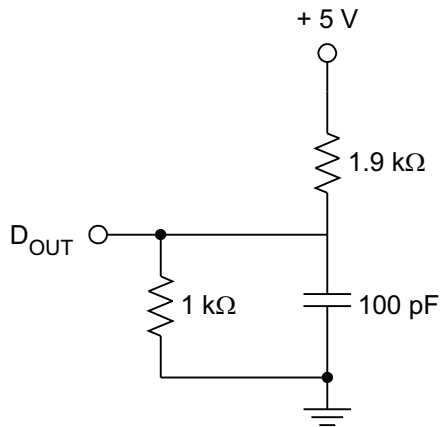


Figure 1. 5-V Output Load A

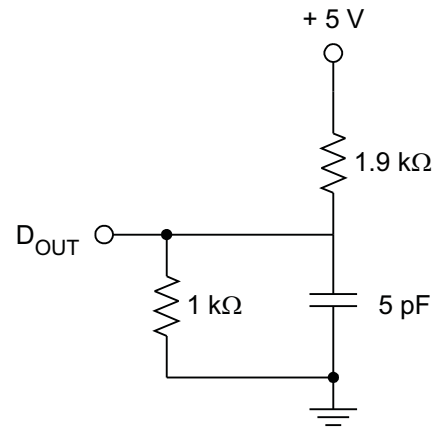


Figure 2. 5-V Output Load A

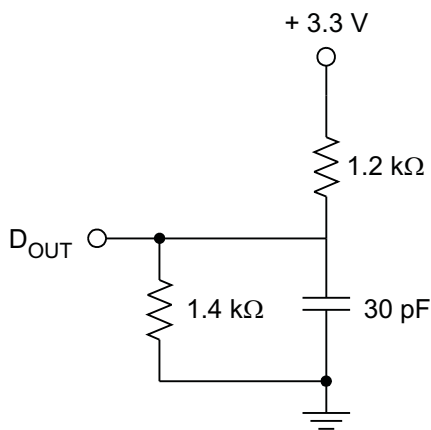


Figure 3. 3.3-V Output Load B

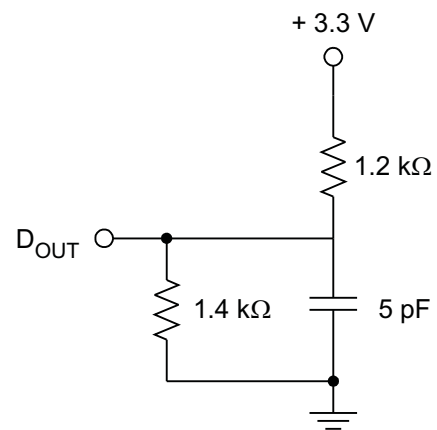
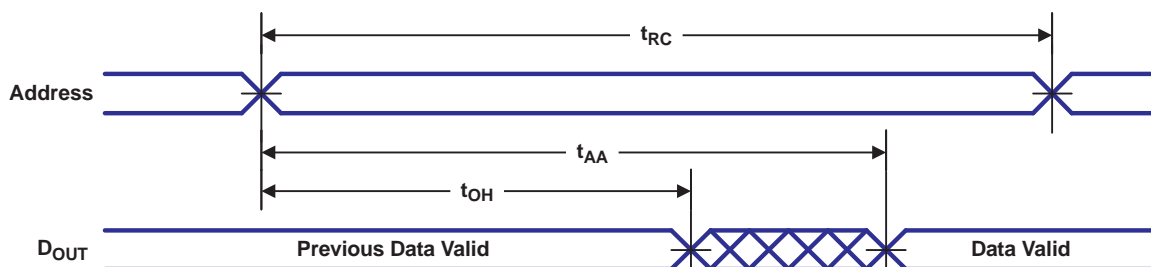


Figure 4. 3.3-V Output Load B

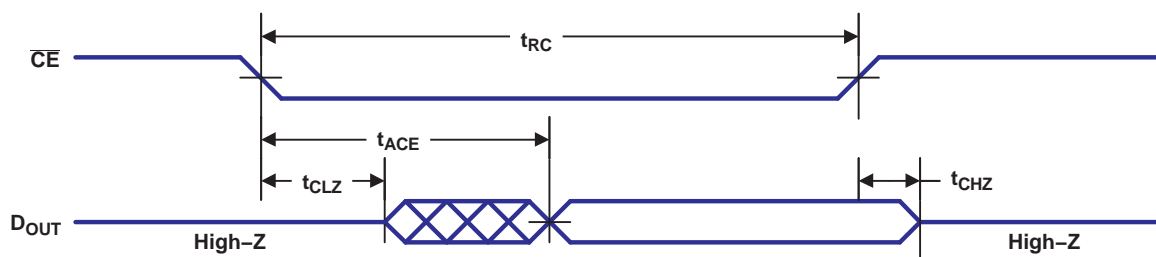
Table 2. READ CYCLE ($T_A = T_{OPR}$, $V_{CC(min)} \leq V_{CC} \leq V_{CC(max)}$)

PARAMETER		TEST CONDITIONS	-70		-85		-150		-200		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{RC}	Read cycle time		70		85		150		200		ns
t_{AA}	Address access time			70		85		150		200	
t_{ACE}	Chip enable access time	Output load A		70		85		150		200	
t_{OE}	Output enable to output valid			35		45		70		90	
t_{CLZ}	Chip enable to output in low Z		5		5		5		5		
t_{OLZ}	Output enable to output in low Z	Output load B	0		0		0		0		
t_{CHZ}	Chip disable to output in high Z		0	25	0	25	0	25	0	25	
t_{OHZ}	Output disable to output in high Z		0	25	0	25	0	25	0	25	
t_{OH}	Output hold from address change	Output load A	10		10		10		10		



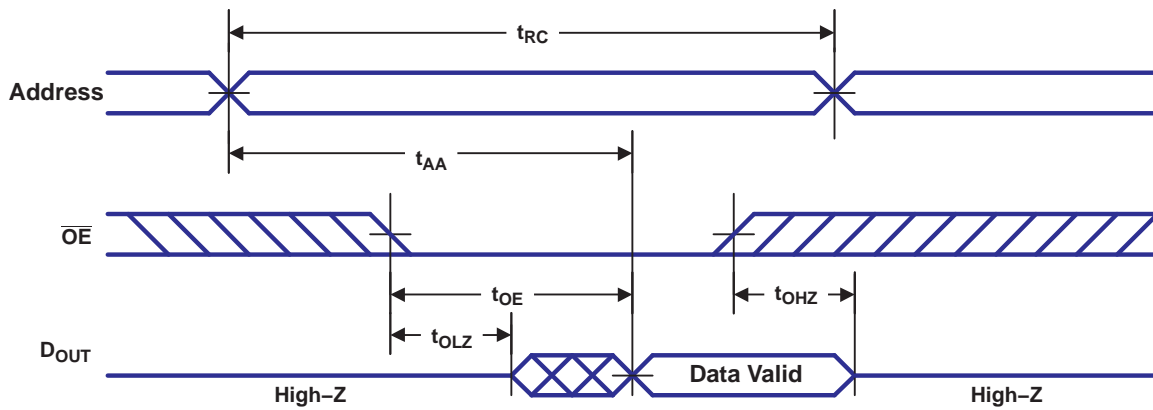
- (1) \overline{WE} is held high for a read cycle.
- (2) Device is continuously selected: $\overline{CE} = \overline{OE} = V_{IL}$.

Figure 5. Read Cycle No. 1 (Address Access) ⁽¹⁾⁽²⁾



- (1) \overline{WE} is held high for a read cycle.
- (2) Device is continuously selected: $\overline{CE} = \overline{OE} = V_{IL}$.
- (3) Address is valid prior to or coincident with \overline{CE} transition low.

Figure 6. Read Cycle No. 2 (\overline{CE} Access) ⁽¹⁾⁽²⁾⁽³⁾



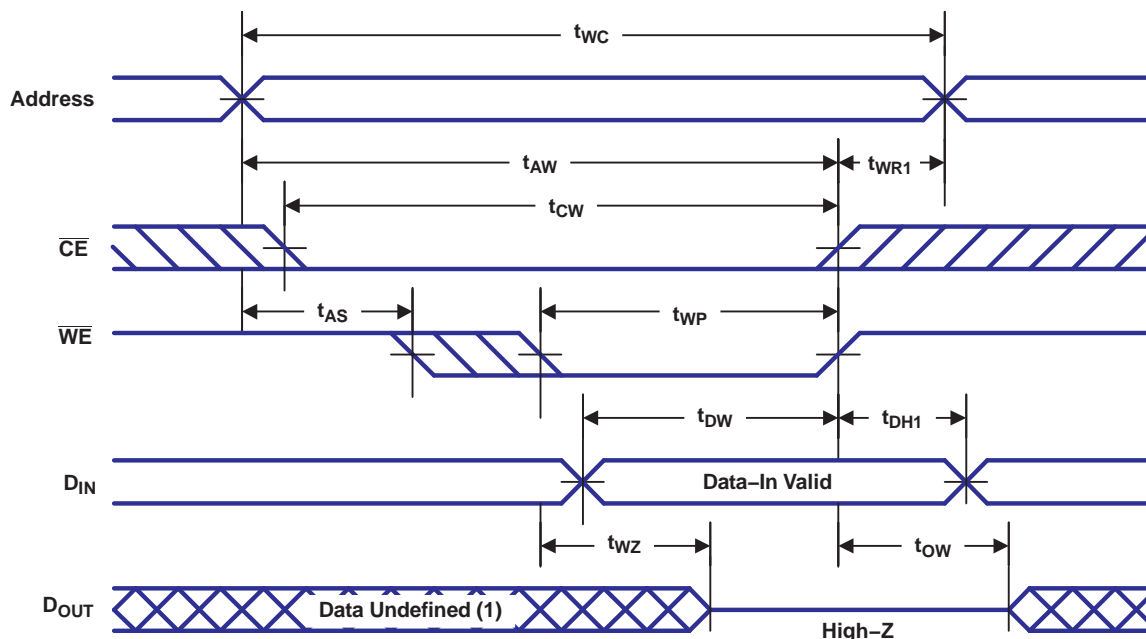
- (1) \overline{WE} is held high for a read cycle.
- (2) Device is continuously selected: $\overline{CE} = V_{IL}$.

Figure 7. Read Cycle No. 3 (\overline{OE} Access) ⁽¹⁾⁽²⁾

Table 3. WRITE CYCLE ($T_A = T_{OPR}$, $V_{CC(min)} \leq V_{CC} \leq V_{CC(max)}$)

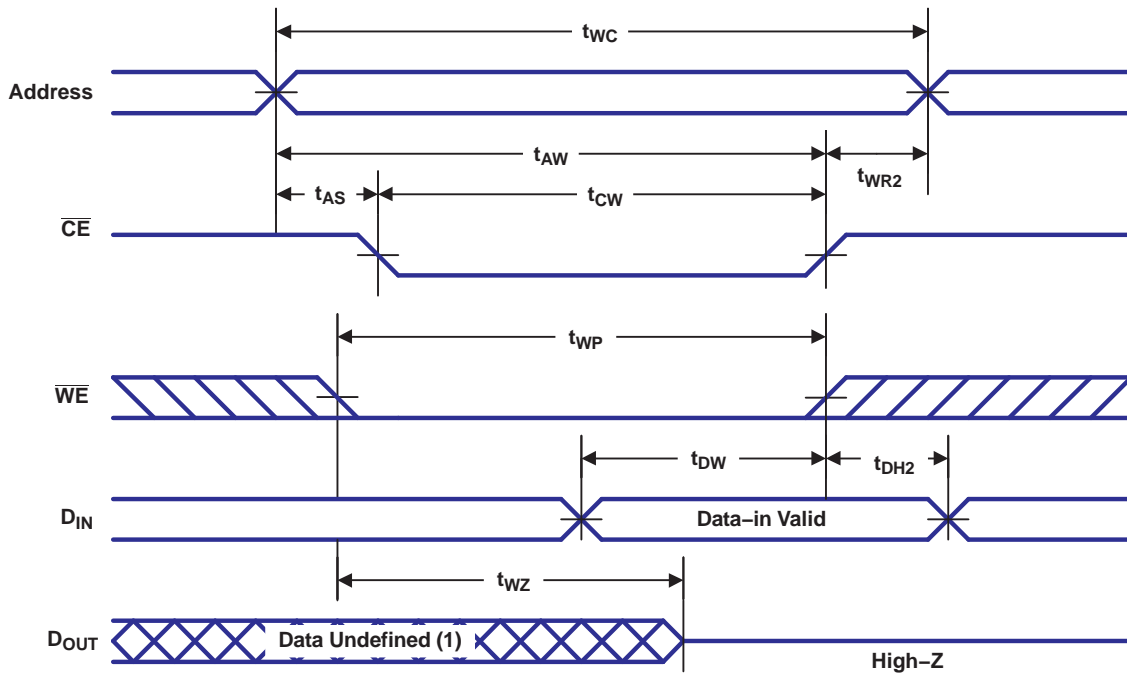
PARAMETER	TEST CONDITIONS	-70		-85		-150		-200		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{WC}	Write cycle time	70		85		150		200		ns
t_{CW}	Chip enable to end of write	65		75		100		150		
t_{AW}	Address valid to end of write	65		75		90		150		
t_{AS}	Address setup time	0		0		0		0		
t_{WP}	Write pulse width	55		65		90		130		
t_{WR1}	Write recovery time (write cycle 1)	5		5		5		5		
t_{WR2}	Write recovery time (write cycle 2)	15		15		15		15		
t_{DW}	Data valid to end of write	30		35		50		70		
t_{DH1}	Data hold time (write cycle 1)	0		0		0		0		
t_{DH2}	Data hold time (write cycle 2)	0		0		0		0		
t_{WZ}	Write enabled to output in high Z	0	25	0	30	0	50	0	70	
t_{OW}	Output active from end of write	5		5		5		5		

- (1) A write ends at the earlier transition of \overline{CE} going high and \overline{WE} going high.
- (2) A write occurs during the overlap of a low \overline{CE} and a low \overline{WE} . A write begins at the later transition of \overline{CE} going low and \overline{WE} going low.
- (3) Either t_{WR1} or t_{WR2} must be met.
- (4) Either t_{DH1} or t_{DH2} must be met.
- (5) If \overline{CE} goes low simultaneously with \overline{WE} going low or after \overline{WE} going low, the outputs remain in high-impedance state.



- (1) \overline{CE} or \overline{WE} must be high during address transition.
- (2) Because I/O may be active (\overline{OE} low) during this period, data input signals of opposite polarity to the outputs must not be applied.
- (3) If \overline{OE} is high, the I/O pins remain in a state of high impedance.

Figure 8. Write Cycle No. 1 (\overline{WE} -Controlled) (1)(2)(3)



- (1) \overline{CE} or \overline{WE} must be high during address transition.
- (2) Because I/O may be active (\overline{OE} low) during this period, data input signals of opposite polarity to the outputs must not be applied.
- (3) If \overline{OE} is high, the I/O pins remain in a state of high impedance.
- (4) Either t_{WR1} or t_{WR2} must be met.
- (5) Either t_{DH1} or t_{DH2} must be met.

Figure 9. Write Cycle No. 2 (\overline{CE} -Controlled) (1)(2)(3)(4)(5)

Table 4. 5-V POWER-DOWN/POWER-UP ($T_A = T_{OPR}$)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t_{PF}	V_{CC} slew, 4.75 to 4.25 V		300			μ s
t_{FS}	V_{CC} slew, 4.25 to V_{SO}		10			μ s
t_{PU}	V_{CC} slew, V_{SO} to V_{PFD} (max.)		0			μ s
t_{CER}	Chip enable recovery time	Time during which SRAM is write-protected after V_{CC} passes V_{PFD} on power-up.	40	80	120	ms
t_{DR}	Data-retention time in absence of V_{CC}	$T_A = 25^\circ\text{C}$ ⁽²⁾	10			years
t_{WPT}	Write-protect time	Delay after V_{CC} slews down past V_{PFD} before SRAM is writeprotected.	40	100	150	μ s

- (1) Typical values indicate operation at $T_A = 25^\circ\text{C}$, $V_{CC} = 5\text{V}$.
 (2) Batteries are disconnected from circuit until after V_{CC} is applied for the first time. t_{DR} is the accumulated time in absence of power beginning when power is first applied to the device.

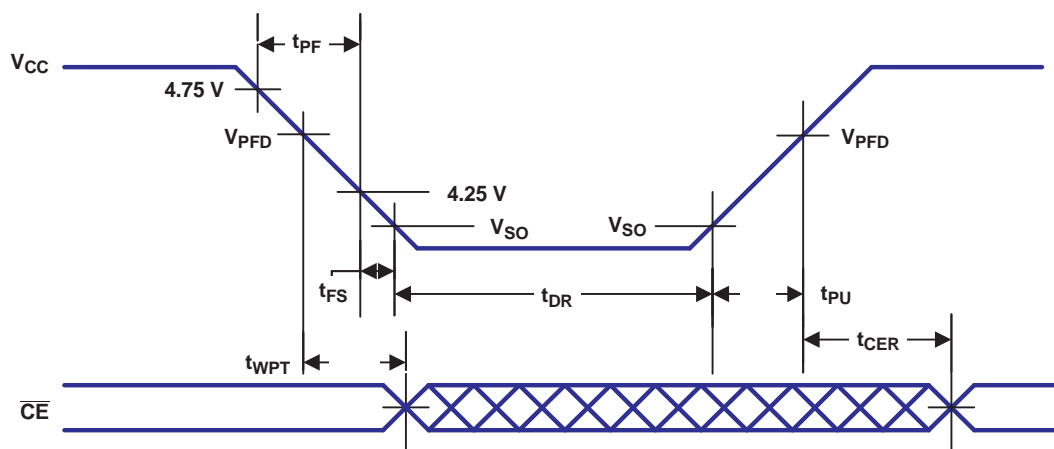


Figure 10. 5-V Power-Down/Power-Up Timing

Table 5. 3.3-V POWER-DOWN/POWER-UP ($T_A = T_{OPR}$)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t_F	V_{CC} slew, 3 V to 0 V		300			μs
t_R	V_{CC} slew, V_{SO} to $V_{PFD(max)}$		100			
t_{CER}	Chip enable recovery time	Time during which SRAM is write-protected after V_{CC} passes V_{PFD} on power-up.	10		85	ms
t_{DR}	Data-retention time in absence of V_{CC}	$T_A = 25^\circ\text{C}^{(2)}$	10			years

- (1) Typical values indicate operation at $T_A = 25^\circ\text{C}$, $V_{CC} = 3.3\text{ V}$.
- (2) Batteries are disconnected from circuit until after V_{CC} is applied for the first time. Data retention time (t_{DR}) is the accumulated time in absence of power beginning when power is first applied to the device.

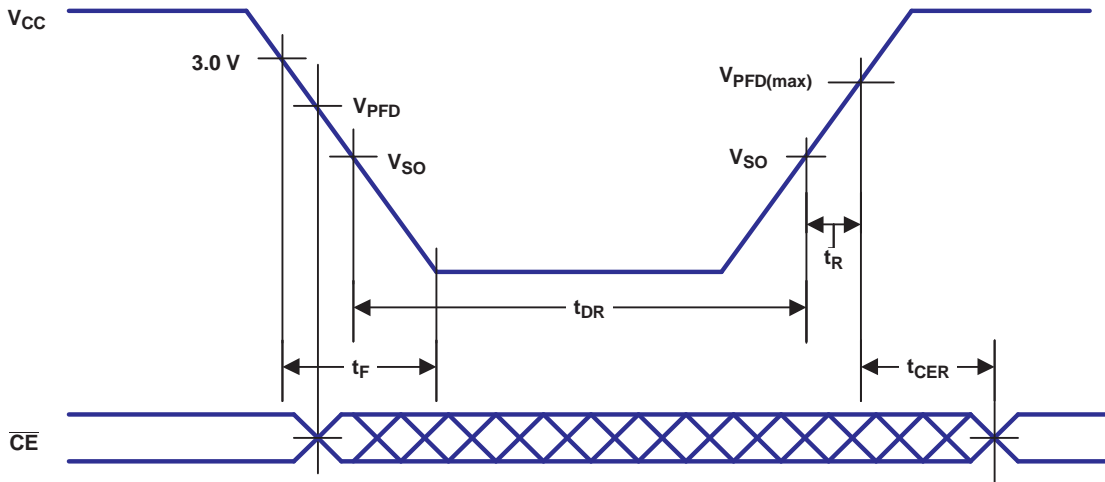


Figure 11. 3.3-V Power-Down/Power-Up Timing

CAUTION:

Negative undershoots below the absolute maximum rating of -0.3 V in battery-backup mode may affect data integrity.

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
BQ4010LYMA-70N	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010MA-150	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010MA-200	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010MA-70	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010MA-85	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010YMA-150	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010YMA-150N	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010YMA-200	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010YMA-70	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010YMA-70N	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010YMA-85	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type
BQ4010YMA-85N	ACTIVE	DIP MOD ULE	MA	28	1	Pb-Free (RoHS)	CU SN	N / A for Pkg Type

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

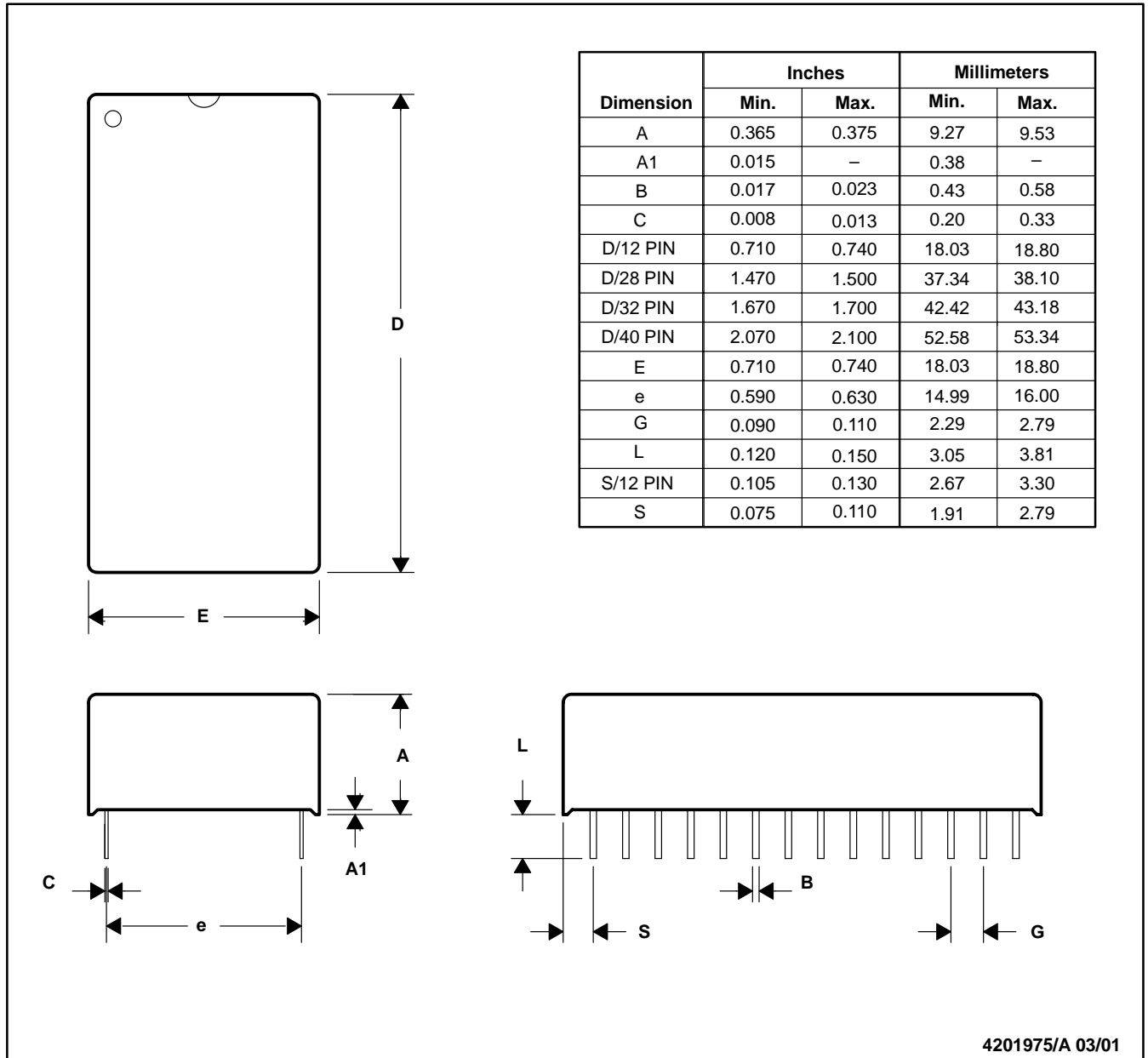
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MA (R-PDIP-T**)

PLASTIC DUAL-IN-LINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in inches (mm).
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